

Hung-Pin Hsu

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/2295222/publications.pdf>

Version: 2024-02-01

41
papers

446
citations

759233

12
h-index

752698

20
g-index

41
all docs

41
docs citations

41
times ranked

853
citing authors

#	ARTICLE	IF	CITATIONS
1	Temperature Dependent Excitonic Transition Energy and Enhanced Electron-Phonon Coupling in Layered Ternary SnS ₂ -xSex Semiconductors with Fully Tunable Stoichiometry. <i>Molecules</i> , 2021, 26, 2184.	3.8	5
2	Humidity Sensing and Photodetection Based on Tin Disulfide Nanosheets. <i>Crystals</i> , 2021, 11, 1028.	2.2	0
3	High Optical Response of Niobium-Doped WSe ₂ -Layered Crystals. <i>Materials</i> , 2019, 12, 1161.	2.9	5
4	Optical Characterization and Photovoltaic Performance Evaluation of GaAs p-i-n Solar Cells with Various Metal Grid Spacings. <i>Crystals</i> , 2019, 9, 170.	2.2	3
5	PbI ₂ Single Crystal Growth and Its Optical Property Study. <i>Crystals</i> , 2019, 9, 589.	2.2	28
6	Optical and electrical transport properties of ZnO/MoS ₂ heterojunction p-n structure. <i>Materials Chemistry and Physics</i> , 2018, 220, 433-440.	4.0	16
7	Effect of Lithium Doping on Microstructural and Optical Properties of ZnO Nanocrystalline Films Prepared by the Sol-Gel Method. <i>Crystals</i> , 2018, 8, 228.	2.2	13
8	Doping with Nb enhances the photoresponsivity of WSe ₂ thin sheets. <i>AIP Advances</i> , 2018, 8, .	1.3	13
9	Anisotropic Spectroscopy and Electrical Properties of 2D ReS ₂ (1- <i>x</i>)Se ₂ <i>x</i> Alloys with Distorted 1T Structure. <i>Small</i> , 2017, 13, 1603788.	10.0	70
10	Temperature-dependent photoluminescence emission and Raman scattering from Mo _{1-x} W _x S ₂ monolayers. <i>Nanotechnology</i> , 2016, 27, 445705.	2.6	48
11	Growth of ZnO and indium-doped ZnO structures for dye-sensitized solar cells. , 2016, , .		0
12	The study of temperature dependent strain in Ge epilayer with SiGe/Ge buffer layer on Si substrate with different thickness. <i>Applied Physics Letters</i> , 2014, 104, 241605.	3.3	5
13	Photoconductivities in monocrystalline layered V ₂ O ₅ nanowires grown by physical vapor deposition. <i>Nanoscale Research Letters</i> , 2013, 8, 443.	5.7	37
14	Characterization of the structural and optical properties of CuIn _{1-x} Ga _x Se ₂ QD thin films by X-ray diffraction. <i>Journal of Luminescence</i> , 2013, 142, 81-85.	3.1	4
15	Characterization of Ge/Si _{0.16} Ge _{0.84} multiple quantum wells on Ge-on-Si virtual substrate using piezoreflectance spectroscopy. <i>Solid State Communications</i> , 2013, 167, 5-9.	1.9	1
16	Photoreflectance Spectroscopy Characterization of Ge/Si _{0.16} Ge _{0.84} Multiple Quantum Wells on Ge Virtual Substrate. <i>Advances in Condensed Matter Physics</i> , 2013, 2013, 1-6.	1.1	2
17	Evidence of Nitrogen Reorganization in GaAsSbN Alloys. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 022605.	1.5	2
18	Raman scattering characterization of Zn _{1-x} Mg _y Be _x Se mixed crystals. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012, 9, 1752-1755.	0.8	0

#	ARTICLE	IF	CITATIONS
19	Optical characterization of Zn _{0.35} Cd _{0.44} Mg _{0.21} Se crystalline alloy by polarization-dependent contactless electroreflectance measurements. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012, 9, 1756-1759.	0.8	0
20	The structural and material properties of Cu(In,Ga)Se ₂ thin films. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012, 9, 1388-1391.	0.8	3
21	Above-room-temperature photoluminescence from a strain-compensated Ge/Si _{0.15} Ge _{0.85} multiple-quantum-well structure. <i>Applied Physics Letters</i> , 2012, 100, .	3.3	18
22	Thermal effect on the electroluminescence of InGaN/GaN multi-quantum-well light-emitting devices. <i>Solid-State Electronics</i> , 2012, 68, 63-67.	1.4	5
23	Deposition and structural characterization of nanostructured RuO ₂ on rutile-TiO ₂ /sapphire(100) templates by reactive radio frequency magnetron sputtering. <i>Thin Solid Films</i> , 2012, 520, 2810-2813.	1.8	1
24	Optical study of GaAs _{1-x} Sb layers grown on GaAs substrates by gas-source molecular beam epitaxy. <i>Materials Chemistry and Physics</i> , 2010, 124, 558-562.	4.0	7
25	Photoluminescence and surface photovoltage spectroscopy characterization of highly strained InGaAs/GaAs quantum well structures grown by metal organic vapor phase epitaxy. <i>Materials Chemistry and Physics</i> , 2010, 124, 1126-1133.	4.0	9
26	Optical studies of type-I GaAs _{1-x} Sb _x /GaAs multiple quantum well structures. <i>Journal of Applied Physics</i> , 2009, 105, 123523.	2.5	10
27	Optical properties of tungsten disulfide single crystals doped with gold. <i>Materials Chemistry and Physics</i> , 2008, 111, 475-479.	4.0	13
28	Photoluminescence and photoreflectance study of annealing effects on GaAs _{0.909} Sb _{0.07} N _{0.021} layer grown by gas-source molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2008, 103, 113508.	2.5	5
29	Raman scattering characterization of well-aligned RuO ₂ nanocrystals grown on sapphire substrates. <i>New Journal of Physics</i> , 2007, 9, 130-130.	2.9	19
30	Well-Aligned IrO_2 Nanocrystals Grown on Sapphire Substrates via Reactive Sputtering. <i>Journal of Nanomaterials</i> , 2007, 2007, 1-17.	2.7	27
31	Optical characterization of Cd _{1-x} Be _x Zn _y Se mixed crystals. <i>Journal of Applied Physics</i> , 2007, 101, 103539.	2.5	11
32	Deposition and characterization of 1D RuO ₂ nanocrystals by reactive sputtering. <i>Journal of Alloys and Compounds</i> , 2007, 442, 310-312.	5.5	10
33	Growth and Characterization of Well-Aligned RuO ₂ Nanocrystals on Oxide Substrates via Reactive Sputtering. <i>Crystal Growth and Design</i> , 2006, 6, 2501-2506.	3.0	22
34	Raman scattering characterization of well-aligned IrO ₂ nanocrystals grown on sapphire substrates via reactive sputtering. <i>Journal of Raman Spectroscopy</i> , 2006, 37, 1411-1415.	2.5	10
35	Modulation spectroscopy study of the effects of growth interruptions on the interfaces of GaAsSb/GaAs multiple quantum wells. <i>Journal of Physics Condensed Matter</i> , 2006, 18, 5927-5935.	1.8	6
36	Device characteristics of GaAs-based heterojunction bipolar transistors using an InGaAs/GaAsP strain-compensated layer as a base material. <i>Semiconductor Science and Technology</i> , 2004, 19, 828-832.	2.0	0

#	ARTICLE	IF	CITATIONS
37	The structural and optical characterization of a new class of dilute nitride compound semiconductors: GaInNP. Journal of Physics Condensed Matter, 2004, 16, S3245-S3256.	1.8	5
38	Observation of spontaneous ordering in the optoelectronic material GaInNP. Applied Physics Letters, 2004, 84, 1299-1301.	3.3	8
39	Temperature dependences of energies and broadening parameters of the band-edge excitons of Re-doped WS ₂ and 2H-WS ₂ single crystals. Journal of Physics Condensed Matter, 2004, 16, 6995-7005.	1.8	19
40	Piezoreflectance and contactless electroreflectance spectra of an optoelectronic material: GaInNP grown on GaAs substrates. Journal of Crystal Growth, 2004, 264, 357-362.	1.5	5
41	Growth and Characterization of Well-Aligned RuO ₂ /TiO ₂ Heteronanostructures on Sapphire (100) Substrates by Reactive Magnetron Sputtering. Solid State Phenomena, 0, 170, 78-82.	0.3	0